

AMENDMENTS TO THE CLAIMS

Listing Of Claims

Claims 1-33 (Canceled)

61 34. (currently amended) A method for fabricating an interconnect for electrically engaging a bumped contact on a semiconductor component comprising:

providing a substrate having a surface;

forming a plurality of leads on the substrate surface configured to electrically engage and support the bumped contact, the leads having terminal portions and support portions;

~~forming~~ etching a recess in the substrate surface configured to such that the leads cantilever the terminal portions over the recess and are configured with the support portions on the surface supporting the terminal portions for movement within the recess during electrical engagement of the bumped contact.

~~and~~

~~forming an outer layer on each lead configured to provide a non bonding surface for the bumped contact.~~

35. (currently amended) The method of claim 34 ~~wherein the~~ further comprising forming outer layers on the terminal portions configured to provide a non bonding surface for the bumped contact.

~~comprises a material selected from the group consisting of Ti, TiSi₂, Al and a conductive polymer.~~

36. (withdrawn) The method of claim 34 wherein forming the plurality of leads comprises attaching a polymer tape to the substrate with the leads formed thereon.

37. (withdrawn) The method of claim 34 wherein forming the plurality of leads comprises etching beams in the substrate within the recess and covering the beams with conductive layers.

38. (currently amended) The method of claim 34 wherein the substrate comprises a semiconductor material and the etching step comprises anisotropic etching.

~~further comprising forming at least one blade on each lead configured to penetrate the bumped contact.~~

39. (currently amended) A method for fabricating an interconnect for electrically engaging a bumped contact on a semiconductor component comprising:

G | providing a substrate having a surface;
forming a metal layer on the ~~substrate~~ surface;
~~forming~~ etching a plurality of ~~blades~~ projections in the metal layer configured to penetrate the bumped contact;
forming an outer layer on the metal layer configured to provide a non-bonding surface for the bumped contact;
forming a plurality of leads in the metal layer configured to electrically engage and support the bumped contact, the leads having terminal portions with the projections thereon and support portions; and
~~each lead including at least one blade, and~~

~~forming~~ etching a recess in the ~~substrate~~ surface ~~such that~~ configured to cantilever the terminal portions ~~the leads are cantilevered over the recess with the support portions on the surface supporting the terminal portions for movement and are configured to move within the recess during electrical engagement of the bumped contact.~~

40. (previously presented) The method of claim 39 wherein the outer layer comprises a conductive polymer.

41. (previously presented) The method of claim 39 wherein the outer layer comprises a material selected from the group consisting of a carbon film and a metal filled silicone.

42. (withdrawn) The method of claim 39 further comprising shaping the leads with a radius of curvature corresponding to a diameter of the bumped contact.

43. (previously presented) The method of claim 39 further comprising forming a connecting segment on the substrate electrically connecting the leads, a conductive via in the substrate in electrical communication with the connecting segment and a contact on the substrate in electrical communication with the conductive via.

44. (withdrawn) A method for fabricating an interconnect for testing a semiconductor component comprising:

61 providing a substrate;
forming a recess in the substrate;
providing a tape comprising a polymer substrate comprising an opening therein and a plurality of leads on the substrate cantilevered over the opening;
aligning the leads with the recess; and
attaching the tape to the substrate with the leads cantilevered over the recess to form a contact for electrically engaging a bumped contact on the component.

45. (withdrawn) The method of claim 44 further comprising providing the tape with an electrical connector configured for electrical connection to test circuitry.

46. (withdrawn) A method for fabricating an interconnect for testing a semiconductor component comprising:

providing a substrate;
etching a recess in the substrate sized and shaped to retain a bumped contact on the component;
etching a plurality of beams within the recess configured to move within the recess and to support the bumped contact within the recess;
etching a plurality of projections on the conductive beams configured to penetrate the bumped contact; and
forming a conductive layer on the beams and the projections to form a contact for electrically engaging the bumped contact.

47. (withdrawn) The method of claim 46 further comprising controlling the etching of the beams step to form the beams with a cantilever length, a width, and a thickness selected to provide a desired spring constant.

61 48. (withdrawn) The method of claim 46 wherein the substrate comprises silicon and further comprising forming an electrically insulating layer on the beams prior to forming the conductive layer.

49. (currently amended) A method for fabricating an interconnect for electrically engaging bumped contacts on a semiconductor component comprising:

providing a substrate;
~~having a surface and an opposing surface;~~

forming a plurality of interconnect contacts on the substrate configured for electrical engagement of the bumped contacts, each interconnect contact comprising a ~~recess in the surface and~~ a plurality of leads having terminal portions and projections on the terminal portions;
~~cantilevered over the recess configured to support a bumped contact for movement in the recess; and~~

etching a plurality of recesses in the substrate proximate to the leads configured to cantilever the

terminal portions of the leads for movement within the recesses during the electrical engagement; and

forming ~~an~~ outer layers on ~~each lead~~ the terminal portions and projections configured to provide non-bonding surfaces for the bumped contacts.

50. (currently amended) The method of claim 49 wherein the outer layers comprise ~~a~~ a conductive polymer.

51. (currently amended) The method of claim 49 wherein the projections comprise blades.

~~further comprising forming at least one blade on each lead configured to penetrate a bumped contact.~~

52. (withdrawn) The method of claim 49 wherein the forming the conductive vias step comprises laser machining.

61 53. (withdrawn) A method for fabricating an interconnect for a semiconductor component having a bumped contact comprising:

providing a substrate having a surface and an opposing surface;

forming a plurality of leads on the surface configured to electrically engage the bumped contact;

forming a connecting segment on the surface electrically connecting the leads;

forming a recess in the surface with the leads cantilevered over the recess and configured to support the bumped contact for movement within the recess;

shaping the leads with a radius of curvature corresponding to a diameter of the bumped contact;

forming a conductive via in the substrate in electrical communication with the connecting segment; and

forming a contact on the opposing surface in electrical communication with the bumped contacts.

54. (withdrawn) The method of claim 53 further comprising forming a plurality of blades on the leads configured to penetrate the bumped contact.

55. (withdrawn) The method of claim 53 wherein the forming the conductive via step comprises laser machining an opening through the connecting segment and the substrate.

56. (withdrawn) The method of claim 53 wherein the contact comprises a pad.

57. (withdrawn) The method of claim 53 wherein the forming the conductive via step comprises electrically insulating and then at least partially filling an opening with a conductive material.

58. (withdrawn) The method of claim 53 wherein the substrate comprises a material selected from the group consisting of silicon, ceramic and plastic.

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Concluded
